IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Applicant:

Yair EIN-ELI et al

Serial No.:

10/750,969

Filed:

January 5, 2004

For:

Texturing A Semiconductor Material ...

Group Art Unit: 1742

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Attorney

Docket: 27054

Commissioner for Patents PO Box 1450 Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT

Sir:

Enclosed is a PTO Form 1449 which lists citations which may be material to the patentability and examination of the above identified application. Also enclosed are copies of the references cited. These are submitted in compliance with the duty of disclosure defined in 37 CFR 1.56. The Examiner is requested to make these citations of official record in this application.

This Information Disclosure Statement under 37 CFR 1.56 is not to be construed as a representation that a search has been made, that additional matter which is material to the examination of this application does not exist, or that any or more of these citations constitutes prior art.

Registration No. 25,457

Date: October 28, 2004

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PTO/SB/08A (10-96)

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> Group Art Unit **Examiner Name**

First Named Inventor

Considered

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

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Sheet	1			Of		2	Attorney Docket Number	27054	
				U.S	S. PATENT	DOCUMENTS		<u> </u>	
Examiners Initials	Cite No. 1	U.S. Patent Document Number Kind Code² (if known)		Name of Patentee or Applicant of Cited Document		Date of Publication of Cited Document MM-DD- YYYY	Pages, columns, lines, V Relevant Passages or Relevant Fi Appear		
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_	2	Of	2	Attorney Docket Number	27054		
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